

Nisha Chugh

List of Publications by Year in descending order

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8
papers

45
citations

2258059

3
h-index

2272923

4
g-index

8
all docs

8
docs citations

8
times ranked

34
citing authors

#	ARTICLE	IF	CITATIONS
1	Polarization dependent charge control model for microwave performance assessment of AlGa _N /Ga _N /AlGa _N double heterostructure HEMTs. Journal of Computational Electronics, 2018, 17, 1229-1240.	2.5	12
2	Sheet carrier concentration and current-voltage analysis of Al _{0.15} Ga _{0.85} N/GaN/Al _{0.15} Ga _{0.85} N double heterostructure hemt incorporating the effect of traps. Microsystem Technologies, 2022, 28, 665-674.	2.0	8
3	Applicability of Field Plate in Double Channel GaN HEMT for Radio-Frequency and Power-Electronic Applications. Silicon, 0, , 1.	3.3	8
4	Sheet carrier concentration and threshold voltage modeling of asymmetrically doped AlGa _N /Ga _N /AlGa _N double heterostructure HEMT. , 2017, , .		7
5	Analysis of Al _{0.15} Ga _{0.85} N/GaN/Al _{0.15} Ga _{0.85} N DH-HEMT for RF and Microwave Frequency Applications. Semiconductors, 2019, 53, 1784-1791.	0.5	5
6	Extraction of admittance parameters of symmetrically doped AlGa _N /Ga _N /AlGa _N DH-HEMT for microwave frequency applications. Microsystem Technologies, 2021, 27, 4065-4072.	2.0	4
7	Impact of Donor Layer Thickness, Doping Concentration and Gate-Width on Gate-Capacitance of AlGa _N /Ga _N Single and Double Heterostructure HEMT for Microwave Frequency Applications. , 2018, , .		1
8	Impact of donor-layer doping & thickness, gate-length and temperature on potential and electron concentration in AlGa _N /Ga _N Double-Heterostructure and Single-Heterostructure HEMT. , 2018, , .		0